

#### **Product Summary**

BVDSS	Rds(on)	ID @TA = +25°C
20V	0.45Ω @V <sub>GS</sub> = 4.5V	0.92A
200	0.6Ω @Vgs = 2.5V	0.8A

## **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for high efficiency power management applications.

# DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Features and Benefits**

- Low On-Resistance
- Low Gate Threshold Voltage VGS(TH) < 1V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **ESD** Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DIODES™ DMN2710UVQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/guality/product-definitions/

#### **Mechanical Data**

- Package: SOT563
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- **Terminal Connections: See Diagram**
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.006 grams (Approximate)



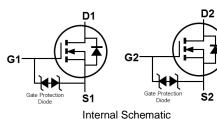
Notes:

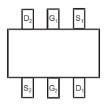
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SOT563

Bottom View





Top View

#### Ordering Information (Note 4)

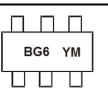
Part Number	Dackage	Packing		
Part Number	Package	Qty.	Carrier	
DMN2710UVQ-7	SOT563	3,000	Tape & Reel	
DMN2710UVQ-13	SOT563	10,000	Tape & Reel	

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

#### **Marking Information**



BG6 = Product Type Marking Code  $\overline{Y}M = Date Code Marking$  $\overline{Y}$  = Year (ex: J = 2022) M = Month (ex: N = November)

Year	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	J	K	L	М	N	0	Р	R	S	Т	U	V
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Top View



### Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characterist	Symbol	Value	Unit	
Drain-Source Voltage		Vdss	20	V
Gate-Source Voltage		V <sub>GSS</sub>	±6	V
Continuous Drain Current (Note 6) $V_{GS} = 4.5V$	ID	0.92 0.74	A	
Maximum Continuous Body Diode Forward Current	ls	0.54	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	)	IDM	5.5	A

#### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	0.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	RθJA	251	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	PD	0.58	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	RθJA	216	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

#### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)			•			
Drain-Source Breakdown Voltage	BVDSS	20	—	—	V	Vgs = 0V, Id = 250µA
Zero Gate Voltage Drain Current $@T_C = +25^{\circ}C$	IDSS	-	—	100	nA	Vds = 20V, Vgs = 0V
Gate-Source Leakage	lgss	-	—	±1.0	μA	$V_{GS} = \pm 4.5 V$ , $V_{DS} = 0 V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.5	—	1.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
			0.13	0.45		Vgs = 4.5V, ID = 600mA
Static Drain-Source On-Resistance	RDS(ON)	—	0.16	0.6	Ω	$V_{GS} = 2.5V, I_{D} = 500mA$
			0.2	0.75		$V_{GS} = 1.8V, I_D = 350mA$
Diode Forward Voltage (Note 7)	V <sub>SD</sub>	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 150mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance		-	42	—	pF	
Output Capacitance	Coss	-	13	—	pF	VDS = 16V, VGS = 0V, f = 1.0MHz
Reverse Transfer Capacitance		_	6.5	_	pF	
Total Gate Charge		_	0.6	—	nC	
Gate-Source Charge		_	0.1	—	nC	VGS = 4.5V, VDS = 10V, D = 250mA
Gate-Drain Charge	Qgd	_	0.1	_	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	4.9	_	ns	
Turn-On Rise Time	t <sub>R</sub>		3.1	—	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$
Turn-Off Delay Time		_	386	—	ns	$R_L = 47\Omega, R_G = 10\Omega$
Turn-Off Fall Time	tF	—	174	—	ns	

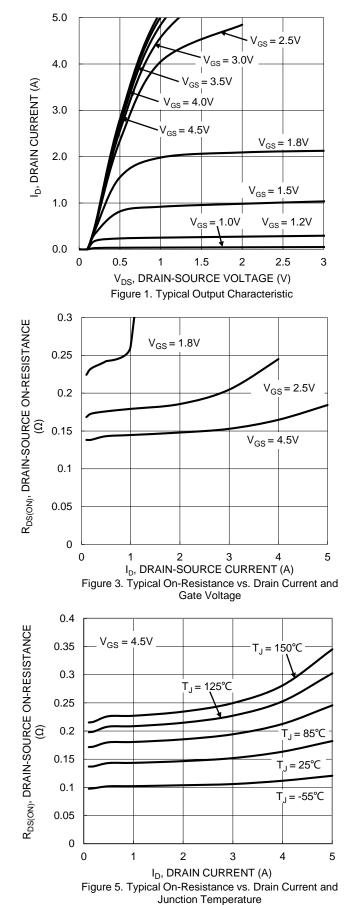
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Device mounted on FR-4 substrate PC board, 202 copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to production testing.



## **DMN2710UVQ**



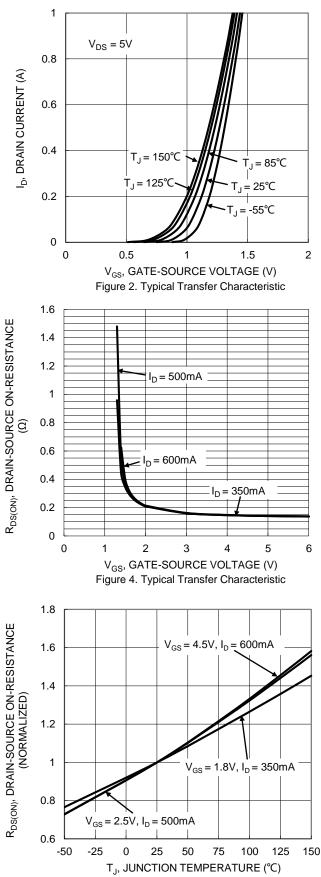
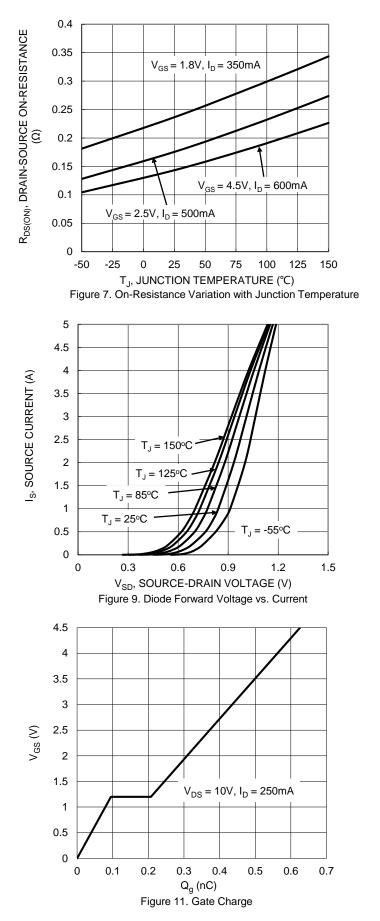
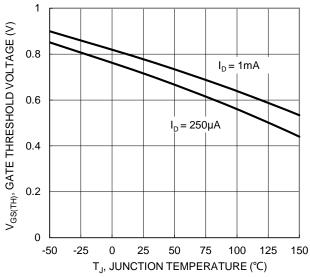


Figure 6. On-Resistance Variation with Junction Temperature

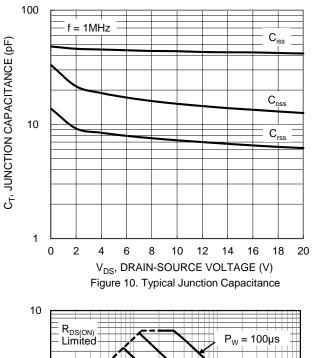


# **DMN2710UVQ**









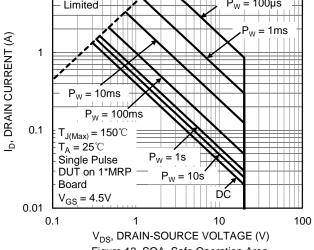
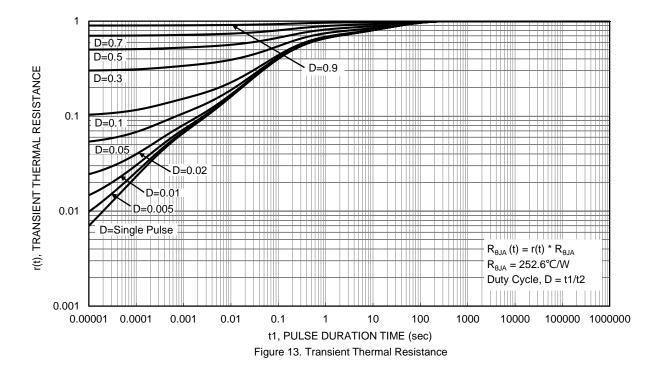


Figure 12. SOA, Safe Operation Area

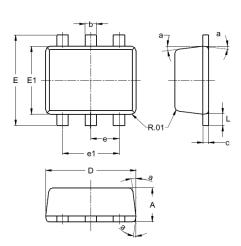






### **Package Outline Dimensions**

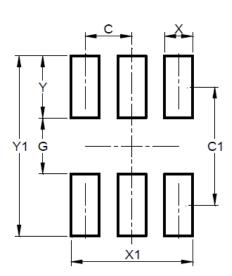
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT563						
Dim	Min	Max	Тур			
Α	0.55	0.60				
b	0.15	0.30	0.20			
С	0.10	0.18	0.11			
D	1.50	1.70	1.60			
Е	1.55	1.70	1.60			
E1	1.10	1.25	1.20			
е			0.50			
e1	0.90	1.10	1.00			
L	0.10	0.30	0.20			
а	8°	9°	7°			
All	Dimens	sions in	mm			

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)			
С	0.500			
C1	1.270			
G	0.600			
Х	0.300			
X1	1.300			
Y	0.670			
Y1	1.940			

SOT563

SOT563



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